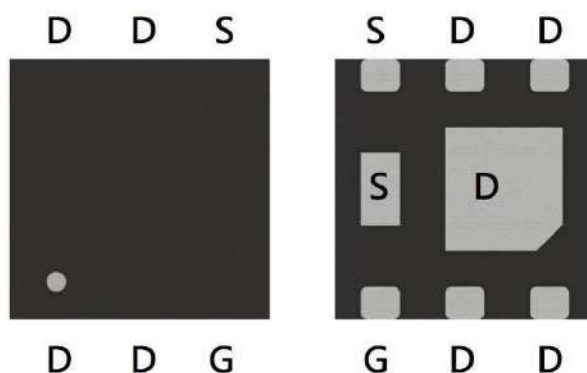


P-Channel Enhancement Mode Power MOSFET

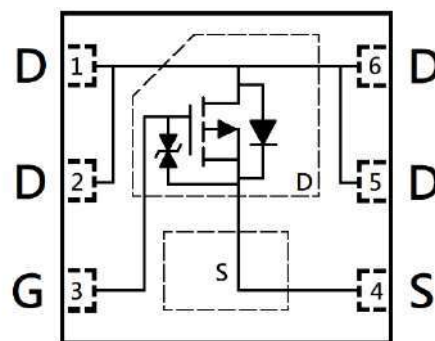
Features:

- Low On Resistance
- Low Gate Charge
- Fast Switching Characteristic
- ESD protected gate, typical 5kV (HBM)

DFNWB2x2-6L-J



BV _{DSS}	-12V
I _D @V _{GS} =-4.5V, T _C =25°C	-14A
I _D @V _{GS} =-4.5V, T _A =25°C	-7.5A
R _{DSON} typ. @V _{GS} =-4.5V, I _D =-7A	12.5mΩ
R _{DSON} typ. @V _{GS} =-2.5V, I _D =-5A	16mΩ
R _{DSON} typ. @V _{GS} =-1.8V, I _D =-3A	24mΩ
R _{DSON} typ. @V _{GS} =-1.5V, I _D =-1A	49mΩ



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KJA12PDF	DFNWB2x2-6L-J (Pb-free lead plating and halogen-free package)	3000 pcs / Tape & Reel

Absolute Maximum Ratings (T_A=25°C)

Parameter	Symbol	Limits	Unit	
Drain-Source Voltage	V _{DS}	-12	V	
Gate-Source Voltage	V _{GS}	±8		
Continuous Drain Current @ V _{GS} =-4.5V, T _C =25°C (silicon limit) *a	I _D	-24	A	
Continuous Drain Current @ V _{GS} =-4.5V, T _C =25°C (package limit) *a		-14		
Continuous Drain Current @ V _{GS} =-4.5V, T _C =100°C *a		-14		
Continuous Drain Current @ V _{GS} =-4.5V, T _A =25°C *b		-7.5		
Continuous Drain Current @ V _{GS} =-4.5V, T _A =70°C *b		-6		
Pulsed Drain Current *c		I _{DM}		-56
Continuous Body Diode Forward Current @ T _C =25°C *a	I _S	-14		
ESD susceptibility	V _{ESD}	5000	V	
Total Power Dissipation	P _D	T _C =25°C *a	17	W
		T _C =100°C *a	6.8	
		T _A =25°C *b	1.7	
		T _A =70°C *b	1.1	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Steady State	Unit
Thermal Resistance, Junction-to-case	R _{θJC}	7.2	°C/W
Thermal Resistance, Junction-to-ambient *b	R _{θJA}	74	

Note:

- *a. The power dissipation P_D is based on T_{J(MAX)}=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
- *b. The value of R_{θJA} is measured with the device mounted on 1 in²FR -4 board with 2 oz. copper, in a still air environment with T_A=25°C. The power dissipation P_D is based on R_{θJA} and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- *c. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and low duty cycles to keep initial T_J=25°C.

Electrical Characteristics (T_A=25°C, unless otherwise specified)

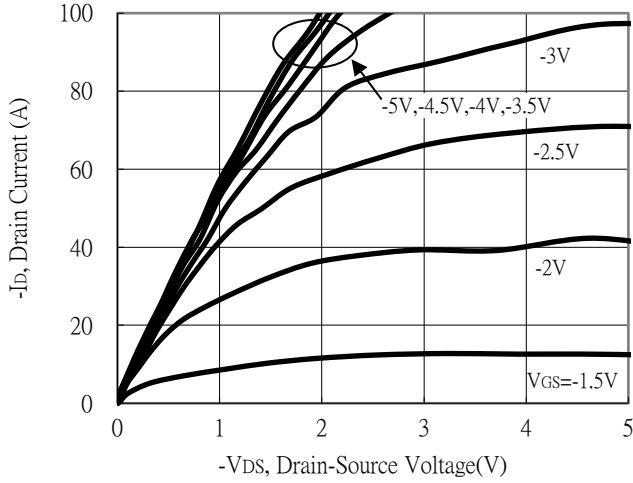
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-12	-	-	V	V _{GS} =0V, I _D =-250μA
V _{GS(th)}	-0.3	-	-1		V _{DS} =V _{GS} , I _D =-250μA
G _{FS}	-	18.7	-	S	V _{DS} =-5V, I _D =-7A
I _{GSS}	-	-	±10	μA	V _{GS} =±8V, V _{DS} =0V
I _{DSS}	-	-	-1		V _{DS} =-8V, V _{GS} =0V
R _{DS(ON)}	-	12.5	18	mΩ	V _{GS} =-4.5V, I _D =-7A
	-	16	25		V _{GS} =-2.5V, I _D =-5A
	-	24	38		V _{GS} =-1.8V, I _D =-3A
	-	49	88		V _{GS} =-1.5V, I _D =-1A
Source-Drain Diode					
V _{SD} *1	-	-0.85	-1.2	V	I _S =-7A, V _{GS} =0V

Note:

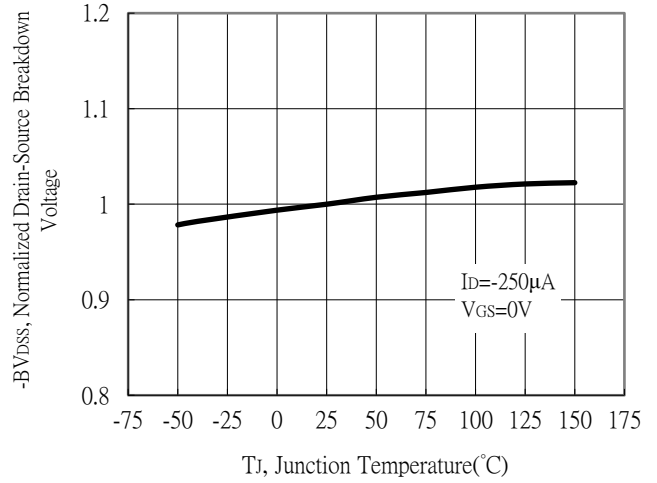
- *1. Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%
- *2. Independent of operating temperature

Typical Characteristics

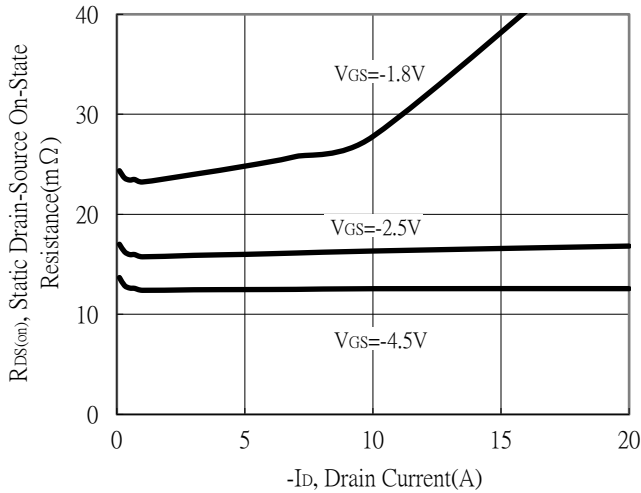
Typical Output Characteristics



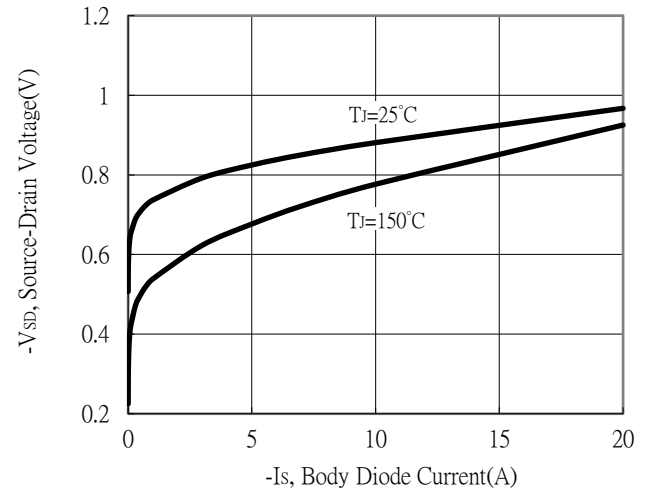
Breakdown Voltage vs Ambient Temperature



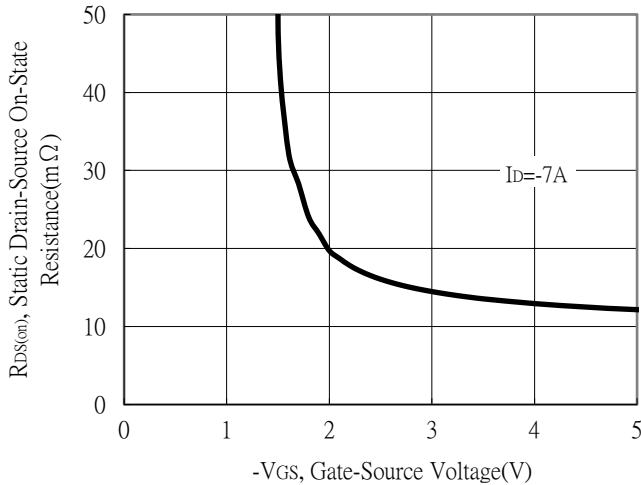
Static Drain-Source On-State resistance vs Drain Current



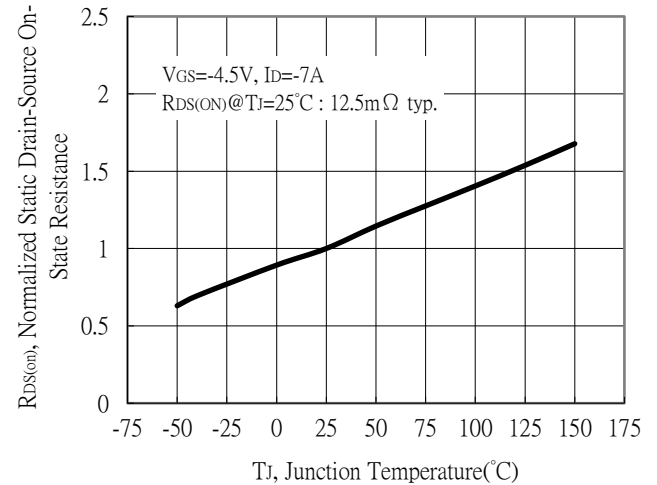
Body Diode Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

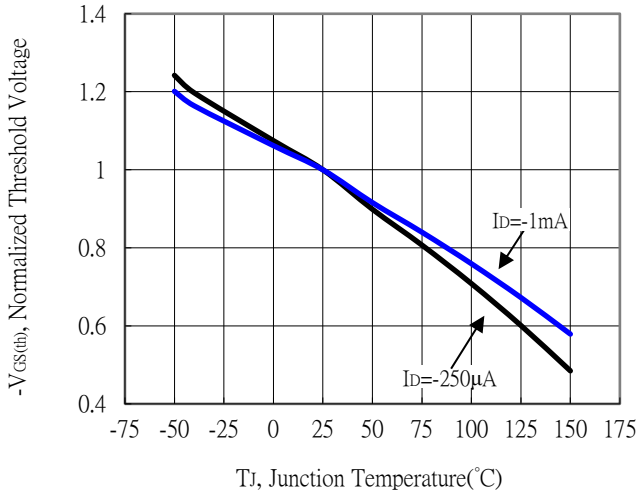


Drain-Source On-State Resistance vs Junction Temperature

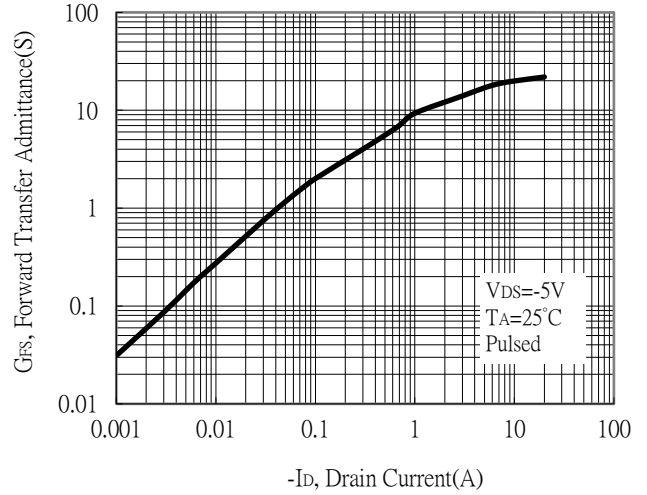


Typical Characteristics (Cont.)

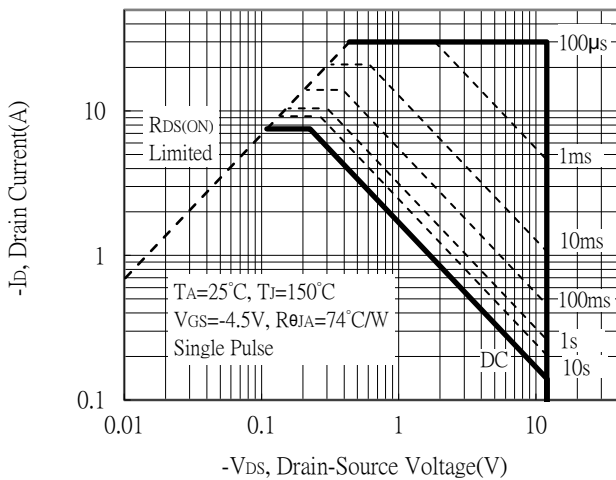
Threshold Voltage vs Junction Temperature



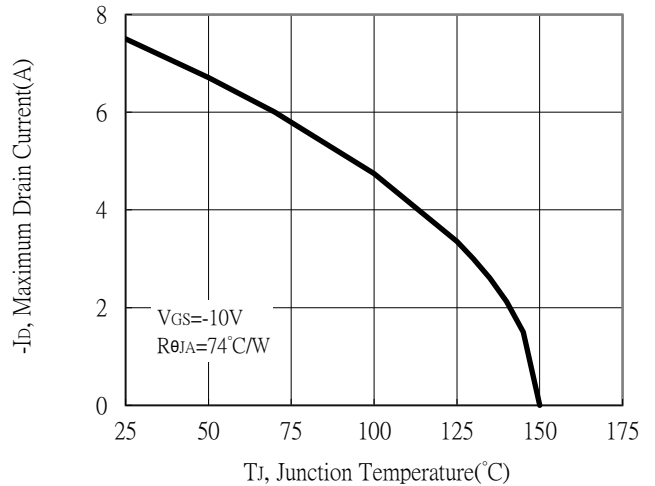
Forward Transfer Admittance vs Drain Current



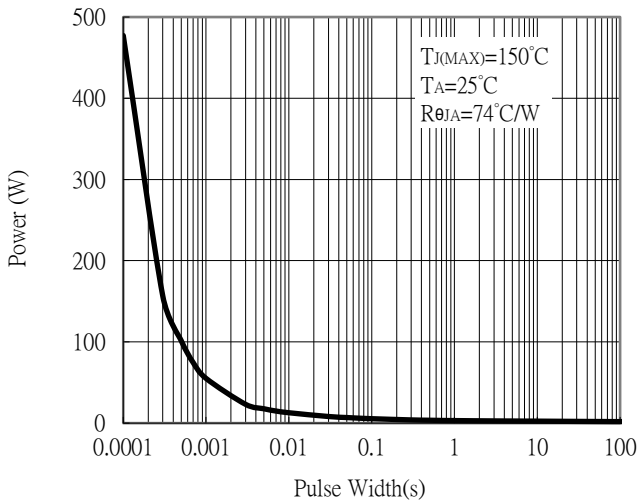
Maximum Safe Operating Area



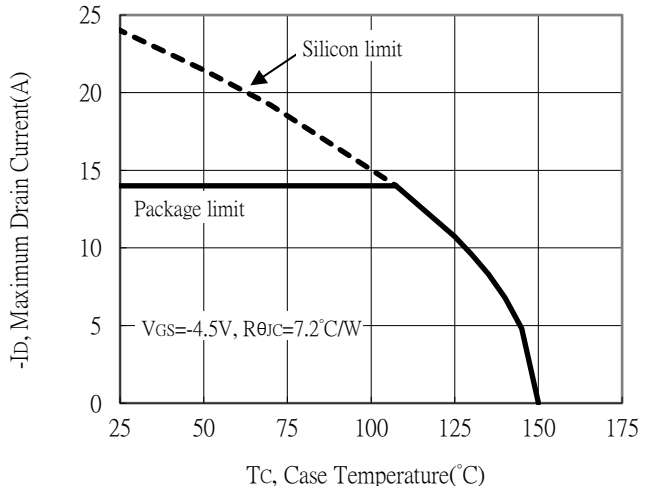
Maximum Drain Current vs Junction Temperature



Single Pulse Power Rating, Junction to Ambient

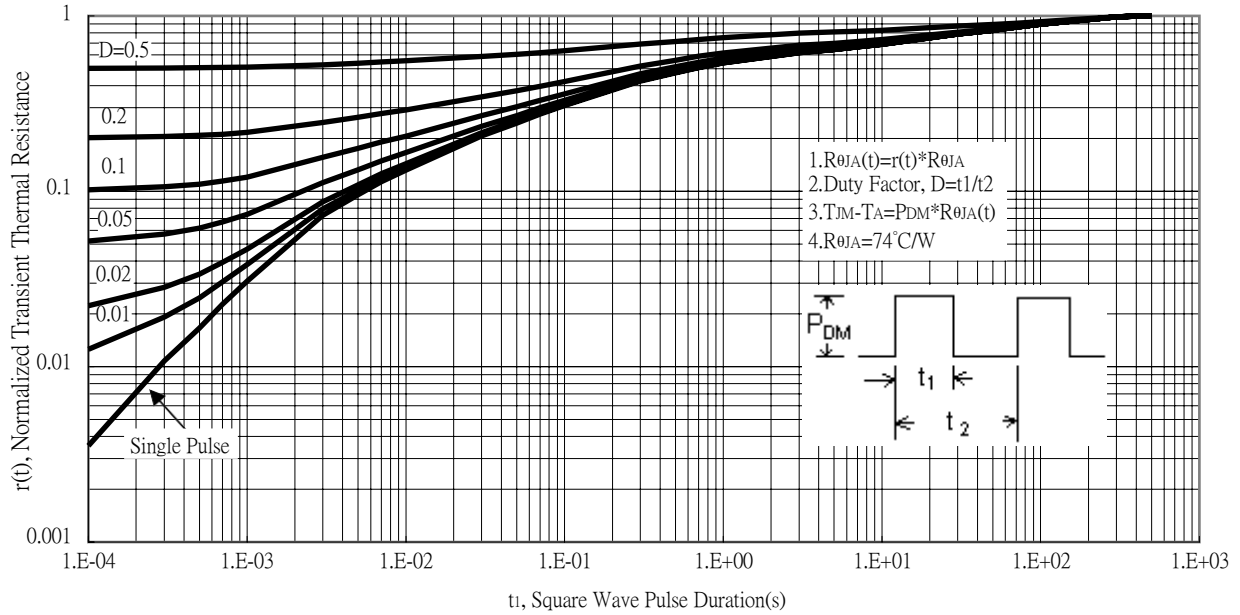


Maximum Drain Current vs Case Temperature

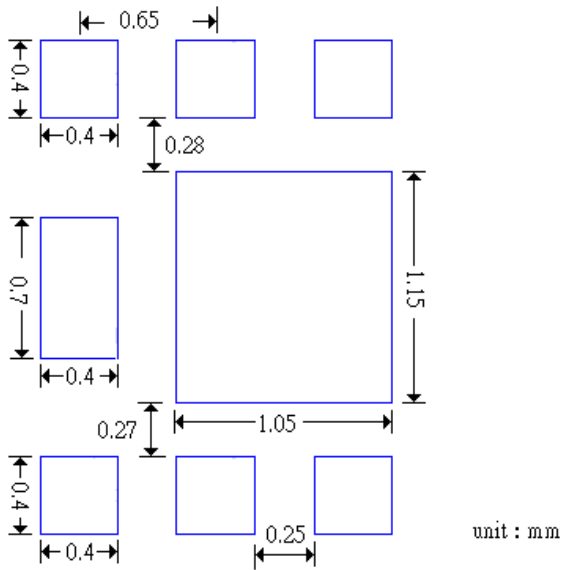


Typical Characteristics (Cont.)

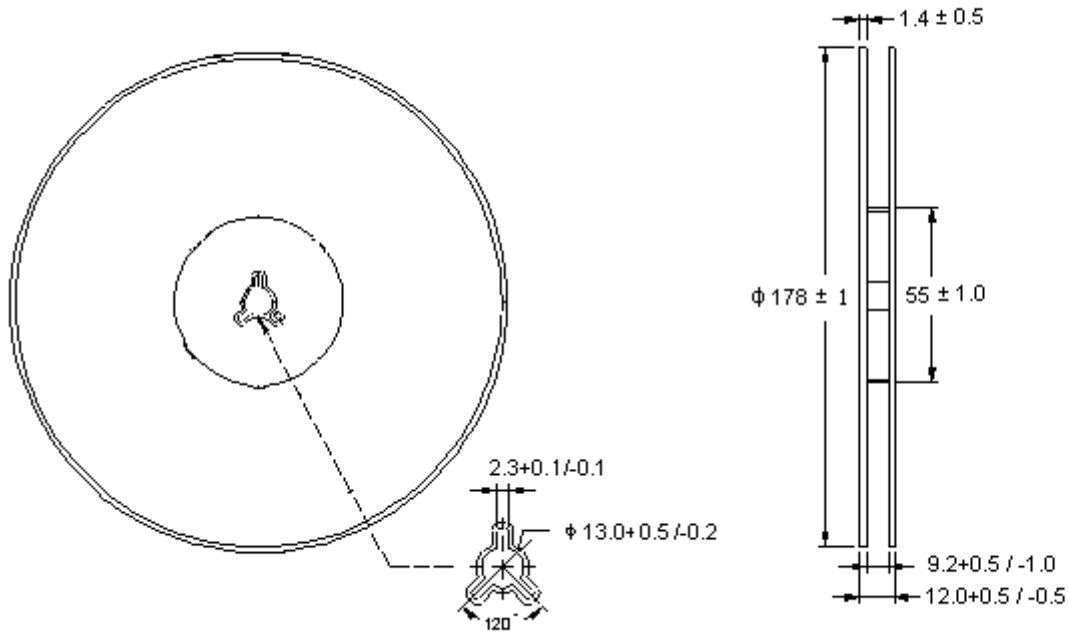
Transient Thermal Response Curves



Recommended Soldering Footprint

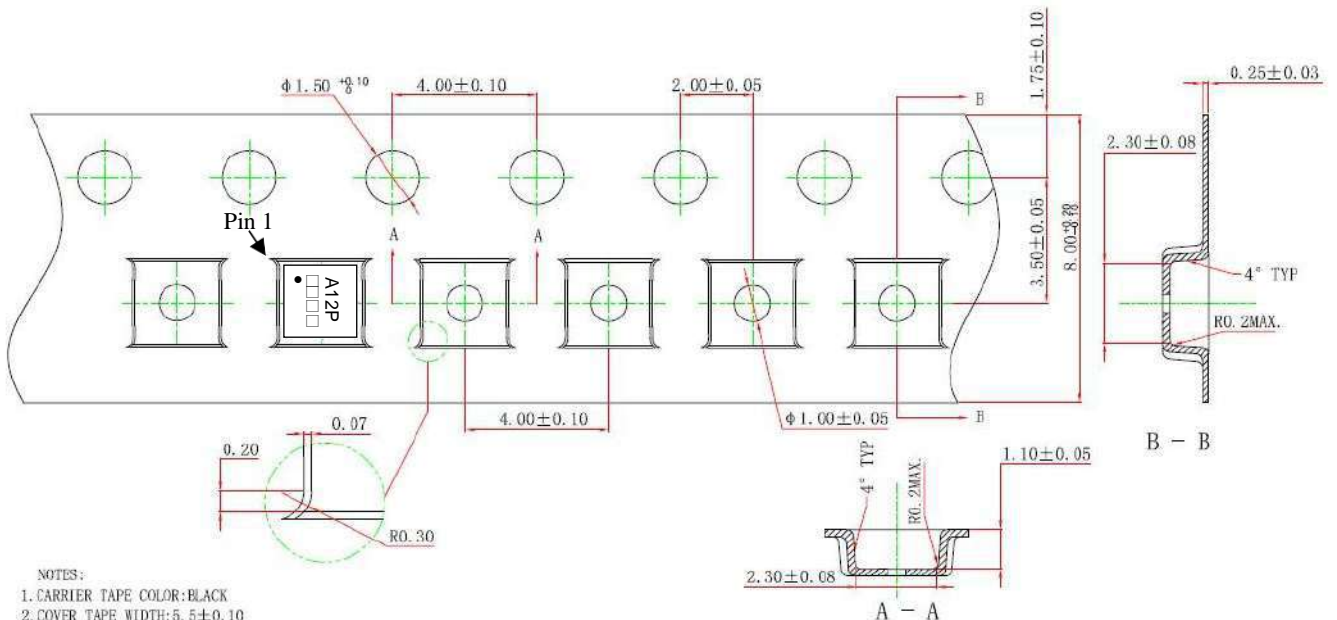


Reel Dimension



Unit: millimeter

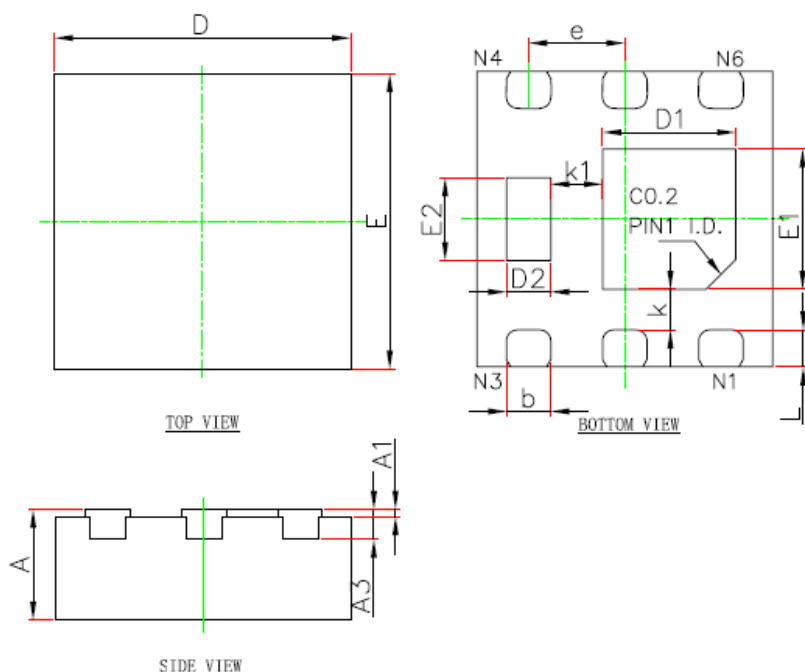
Carrier Tape Dimension



NOTES:

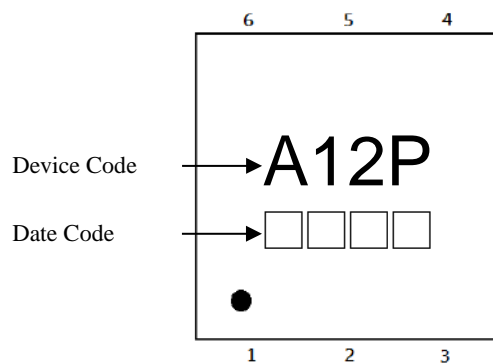
1. CARRIER TAPE COLOR: BLACK
2. COVER TAPE WIDTH: 8.5 ± 0.10
3. COVER TAPE COLOR: TRANSPARENT
4. 1.0 SPROCKET HOLE PITCH CUMULATIVE TOLERANCE ± 0.10 MAX.
5. CAMBER NOT TO EXCEED 1 MM IN 100 MM
6. ALL DIMS IN mm.
7. THE DIRECTION OF VIEW:

DFNWB2x2-6L-J Dimension



6-Lead DFNWB2x2-6L-J Plastic Surface Mounted Package

Marking:



Style: Pin 1.Drain 2.Drain 3.Gate
 4.Source 5.Drain 6.Drain

Date Code(counting from left to right) :
 1st code: year code, the last digit of Christian year
 2nd code : month code, Jan→A, Feb→B, Mar→C,
 Apr→D, May→E, Jun→F, Jul→G, Aug→H,
 Sep→J, Oct→K, Nov→L, Dec→M
 3rd and 4th codes : production serial number, 01~99

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031	D2	0.200	0.400	0.008	0.016
A1	0.000	0.050	0.000	0.002	E2	0.460	0.660	0.018	0.026
A3	0.203	REF	0.008	REF	b	0.250	0.350	0.010	0.014
D	1.900	2.100	0.075	0.083	e	0.650 BSC		0.026 BSC	
E	1.900	2.100	0.075	0.083	k	0.275 REF		0.011 REF	
D1	0.800	1.000	0.031	0.039	k1	0.350 REF		0.014 REF	
E1	0.850	1.050	0.033	0.041	L	0.174	0.326	0.007	0.013